

### **Features**

- Low R<sub>DS(on)</sub> & FOM
- · Extremely Low Switching Loss
- · Excellent Stability and Uniformity
- · Fast Switching and Soft Recovery
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Halogen Free. "Green" Device
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1

# **Maximum Ratings**

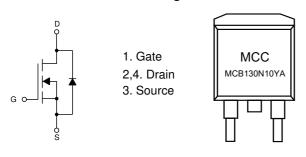
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 60°C/W Junction to Ambient<sup>(1)</sup>
- Thermal Resistance: 0.5°C/W Junction to Case

Parameter	Symbol	Value
Drain-Source Voltage	$V_{DS}$	100V
Gate-Source Volltage	$V_{GS}$	±20V
Continuous Drain Current <sup>(2)</sup> ,T <sub>C</sub> =25°C	I <sub>D</sub>	130A
Pulsed Drain Current <sup>(3)</sup> , T <sub>C</sub> =25°C	I <sub>D,pluse</sub>	440A
Power Dissipation <sup>(4)</sup> , T <sub>C</sub> =25°C	P <sub>D</sub>	260W
Single Pulsed Avalanche Energy <sup>(5)</sup>	E <sub>AS</sub>	900mJ

# Note:

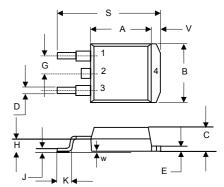
- 1. The Value of  $R_{\theta JA}$  is Measured with the Device Mounted on 1 in<sup>2</sup> FR-4 Board with 2oz. Copper, In a Still Air Environment with  $T_A$ =25°C.
- 2. Calculated Continuous Current Based on Maximum Allowable Junction Temperature.
- 3. Repetitive Rating: Pulse Width Limited By Max. Junction Temperature.
- 4. Pd is Based on Max. Junction Temperature, Using Junction-Case Thermal Resistance.
- 5.  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ , L=2mH, Starting  $T_J$ =25 $^{\circ}$ C.

# **Internal Structure and Marking Code**



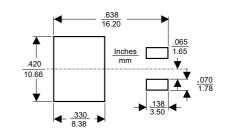
# N-Channel MOSFET

# D2-PAK



DIMENSIONS						
DIM IN		HES	MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.331	0.370	8.40	9.40		
В	0.378	0.417	9.60	10.60		
С	0.165	0.189	4.20	4.80		
D	0.027	0.037	0.68	0.94		
Е	0.045	0.055	1.14	1.40		
G	0.010		2.54		TYP.	
Н	0.096	0.134	2.43	3.40		
J	0.011	0.025	0.28	0.64		
K	0.071	0.131	1.80	3.32		
S	0.575	0.625	14.60	15.87		
V	0.042	0.058	1.07	1.47		
W	0.000	0.010	0.00	0.25		

#### Suggested Solder Pad Layout

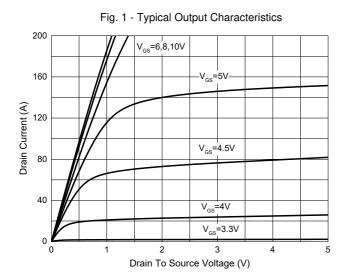


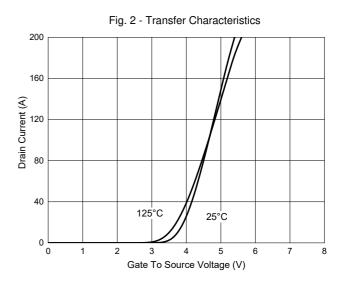


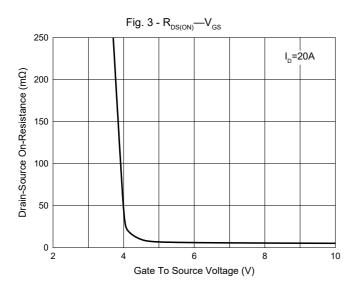
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics						<u>I</u>
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	2	2.8	4	V
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		3.8	4.6	mΩ
Gate Resistance	R <sub>G</sub>	f=1MHz, Open Drain		0.9		Ω
Dynamic Characteristics			,	•		
Drain-Source On-Voltage	C <sub>iss</sub>			4600		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ =0V, $V_{DS}$ =50V,f=1MHz		1250		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			43		pF
Turn-On Delay Time	t <sub>d(on)</sub>			17.6		ns
Rise Time	t <sub>r</sub>	$V_{GS}$ =10V, $V_{DS}$ =50V, $R_{G}$ =2.2 $\Omega$ , $I_{D}$ =20 A		30.2		ns
Turn-Off Delay Time	t <sub>d(off)</sub>			33.5		ns
Fall Time	t <sub>f</sub>			39.5		ns
Gate Charge Characteristics						<u>I</u>
Total Gate Charge	Qg			66		nC
Gate-Source Charge	Q <sub>gs</sub>	VGS=10V,V <sub>DS</sub> =50V,I <sub>D</sub> =20A		23		nC
Gate-Drain Charge	Q <sub>gd</sub>			6.6		nC
<b>Body Diode Characteristics</b>					I.	1
Diode Forward Current	Is	$V_{GS}$ < $V_{th}$			130	А
Pulsed Source Current	I <sub>SP</sub>	▼GS ¬▼th			440	Α
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V			1.3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> =20A,di/dt=100A/μs		63		ns
Reverse Recovery Charge	Q <sub>rr</sub>	15-204,41/41-100A/45		93		nC

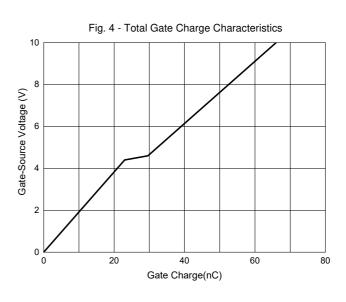


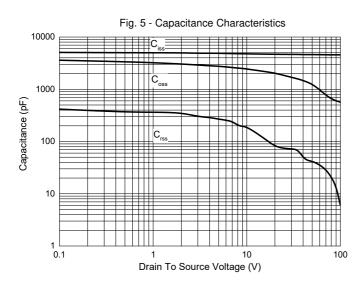
# **Curve Characteristics**

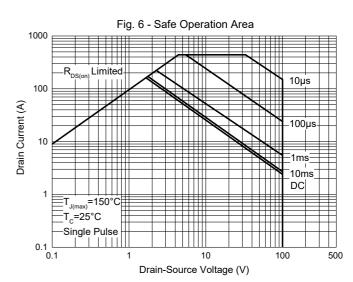














# **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 800pcs/Reel	
Part Number-BP	Tube: 5Kpcs/Ctn	

#### \*\*\*IMPORTANT NOTICE\*\*\*

**Micro Commercial Components Corp.** reserves the right to make changes without further notice to any product herein to make corrections, modifications, enhancements, improvements, or other changes. **Micro Commercial Components Corp**. does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold **Micro Commercial Components Corp**, and all the companies whose products are represented on our website, harmless against all damages. **Micro Commercial Components Corp**, products are sold subject to the general terms and conditions of commercial sale, as published at

https://www.mccsemi.com/Home/TermsAndConditions.

#### \*\*\*LIFE SUPPORT\*\*\*

MCC's products are not authorized for use as critical components in life support devices or systems without the express written approval of Micro Commercial Components Corporation.

# \*\*\*CUSTOMER AWARENESS\*\*\*

Counterfeiting of semiconductor parts is a growing problem in the industry. Micro Commercial Components (MCC) is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. MCC strongly encourages customers to purchase MCC parts either directly from MCC or from Authorized MCC Distributors who are listed by country on our web page cited below. Products customers buy either from MCC directly or from Authorized MCC Distributors are genuine parts, have full traceability, meet MCC's quality standards for handling and storage. MCC will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. MCC is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

Rev.3-4-05112022 4/4 MCCSEMI.COM